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Correction: High-k double gate junctionless tunnel FET with a tunable bandgap

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Correction for 'High-k double gate junctionless tunnel FET with a tunable bandgap' by Shiromani Balmukund Rahi *et al.*, *RSC Adv.*, 2015, 5, 54544–54550.

The authors apologise for the errors in eqn (3). The correct equation is as follows:

$$E_g^{\text{SiGe}} = 1.084 - 0.42x \quad (3)$$

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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